

SANYO Semiconductors DATA SHEET

NPN Triple Diffused Planar Silicon Transistor

2SC5793 — Ultrahigh-Definition CRT Display **Horizontal Deflection Output Applications**

Features

- · High speed.
- High breakdown voltage (V_{CBO}=1600V).
- High reliability (Adoption of HVP process).
- · Adoption of MBIT process.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		1600	V
Collector-to-Emitter Voltage	VCEO		800	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		20	Α
Collector Current (Pulse)	ICP		40	Α
Collector Dissipation	PC		3.0	W
	"	Tc=25°C	95	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ІСВО	V _{CB} =800V, I _E =0A			10	μΑ
Collector Cutoff Current	ICES	VCE=1600V, RBE=0Ω			1.0	mA
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=10mA, RBE=∞	800			V
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0A			1.0	mA
DC Current Gain	hFE1	VCE=5V, IC=1A	10			
	hFE2	V _{CE} =5V, I _C =15A	4		7	

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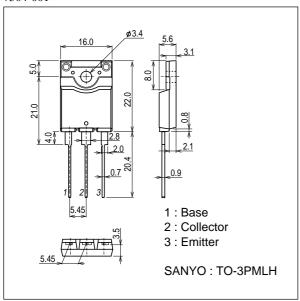
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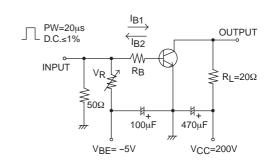
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=13.5A, IB=3.4A			3	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =13.5A, I _B =3.4A			1.5	V
Storage Time	tstg	IC=10A, IB1=1.6A, IB2=-5A			3.0	μS
Fall Time	tf	IC=10A, IB1=1.6A, IB2=-5A			0.2	μS

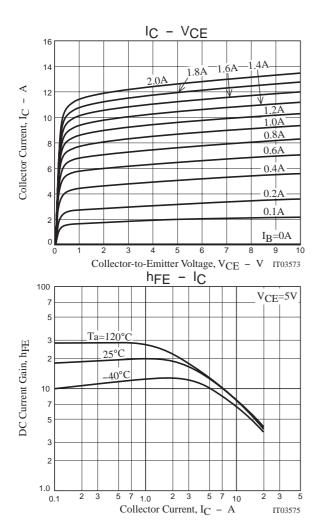
Package Dimensions

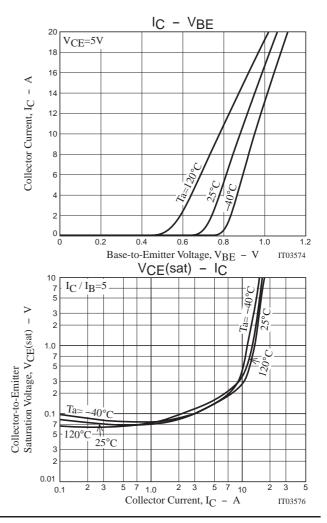
unit : mm (typ) 7504-001

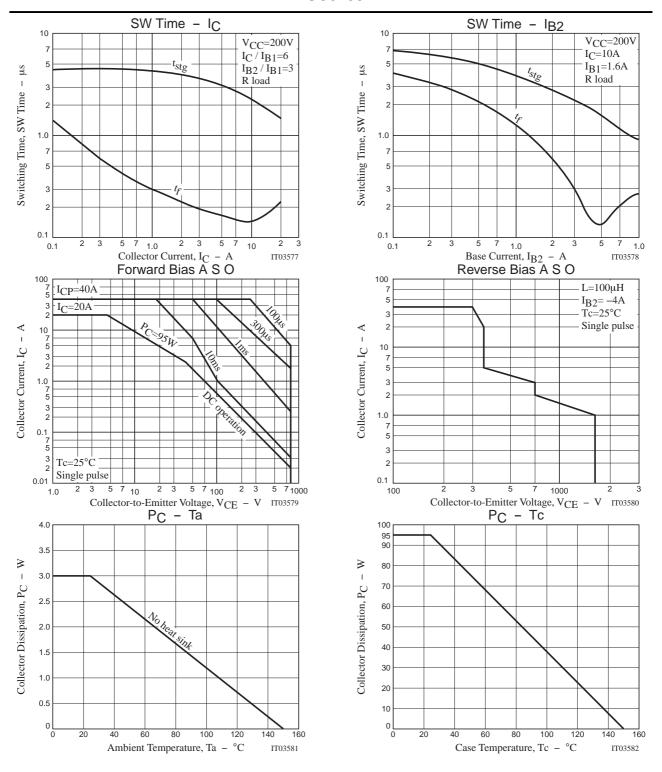


Switching Time Test Circuit









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